

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	1.15mΩ@10V	340A
	1.5mΩ@4.5V	



合肥矽普半导体

Siliup Semiconductor Technology Co., Ltd

技术 品质 服务

www.siliup.com

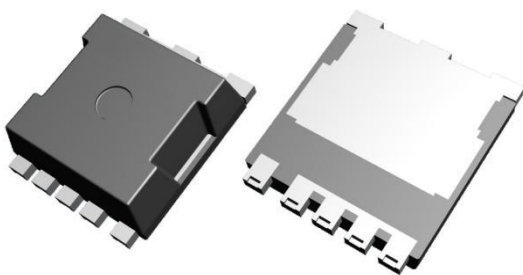
Feature

- Fast Switching
- Low Gate Charge and $R_{DS(on)}$
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

Applications

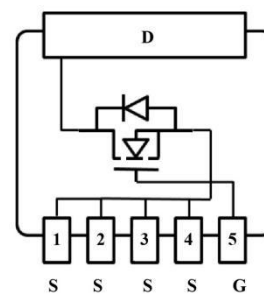
- PWM Application
- Hard switched and high frequency circuits
- Power Management

Package

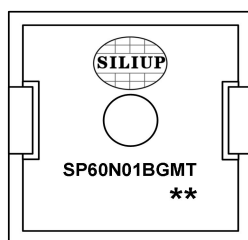


sTOLL

Circuit diagram



Marking



SP60N01BGMT :Device Code
** :Week Code

Order Information

Device	Package	Unit/Tape
SP60N01BGMT	sTOLL	2000

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Tc=25°C)	I_D	340	A
Continuous Drain Current (Tc=100°C)	I_D	227	A
Pulsed Drain Current	I_{DM}	1360	A
Single Pulse Avalanche Energy ¹	E_{AS}	1488	mJ
Total Power Dissipation (Tc=25°C)	P_D	360	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	0.35	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

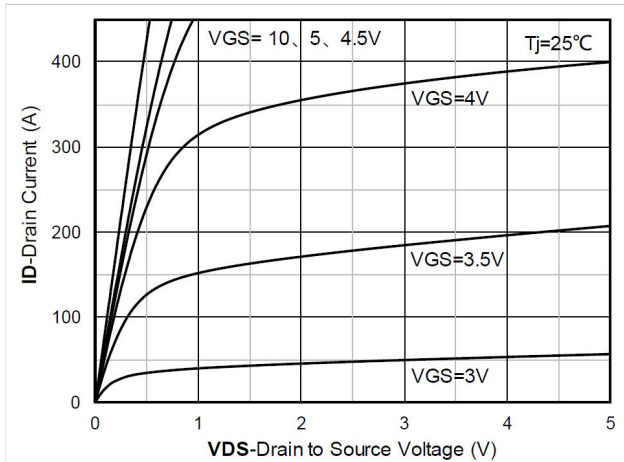
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=250uA	60	-	-	V
Drain-Source Leakage Current	IDSS	VDS=48V , VGS=0V , TJ=25℃	-	-	1	uA
Gate-Source Leakage Current	IGSS	VGS=±20V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VGS=VDS , ID =250uA	1	1.7	2.5	V
Static Drain-Source On-Resistance	RDS(ON)	VGS=10V , ID=50A	-	1.15	1.45	mΩ
		VGS=4.5V , ID=50A	-	1.5	2	
Dynamic characteristics						
Input Capacitance	Ciss	VDS=20V , VGS=0V , f=1MHz	-	7820	-	pF
Output Capacitance	Coss		-	2170	-	
Reverse Transfer Capacitance	Crss		-	88	-	
Total Gate Charge	Qg	VDS=20V , VGS=10V , ID=85A	-	138	-	nC
Gate-Source Charge	Qgs		-	39	-	
Gate-Drain Charge	Qgd		-	32	-	
Switching Characteristics						
Turn-On Delay Time	Td(on)	VDD=20V , VGS=10V , RG=1.6Ω, ID=85A	-	18	-	nS
Rise Time	Tr		-	72	-	
Turn-Off Delay Time	Td(off)		-	108	-	
Fall Time	Tf		-	78	-	
Diode Characteristics						
Diode Forward Voltage	VSD	VGS=0V , IS=1A , TJ=25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	IS		-	-	340	A
Reverse Recovery Time	Trr	IS=50A, di/dt=100A/us, TJ=25℃	-	65	-	nS
Reverse Recovery Charge	Qrr		-	53	-	nC

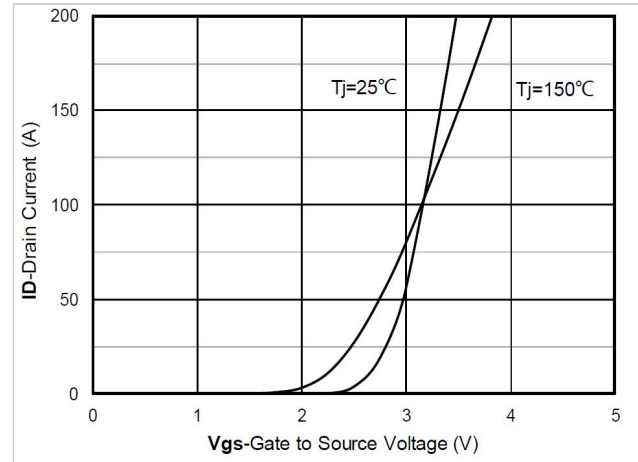
Note :

1. The test condition is $V_{DD}=20V, V_{GS}=10V, L=0.5mH, R_G=25\Omega$

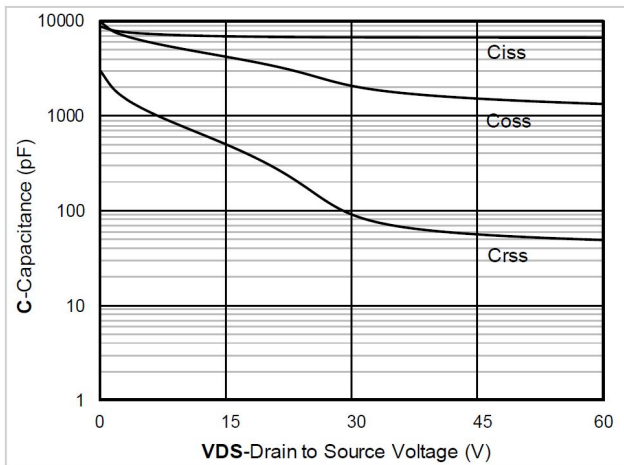
Typical Characteristics



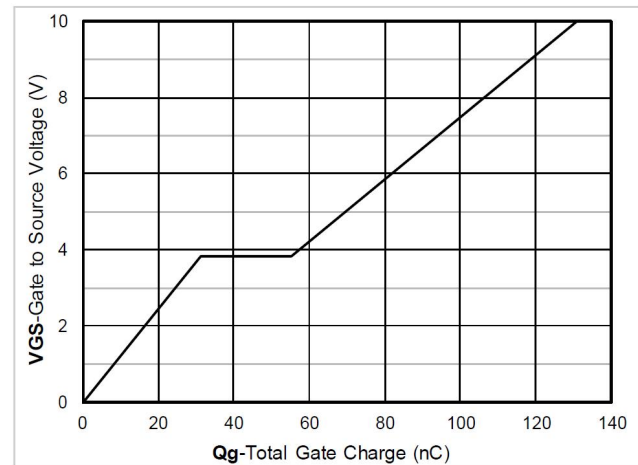
Output Characteristics



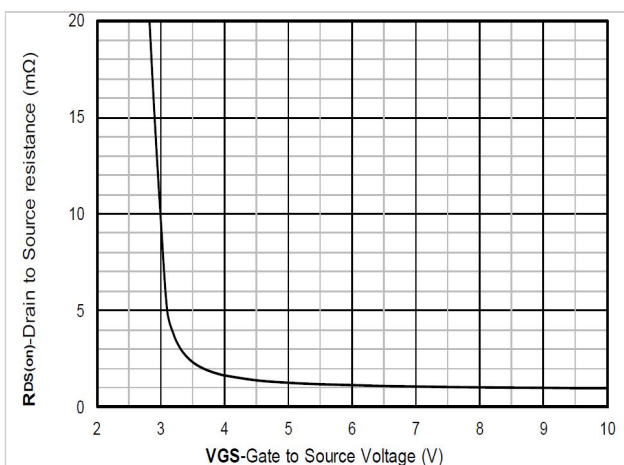
Transfer Characteristics



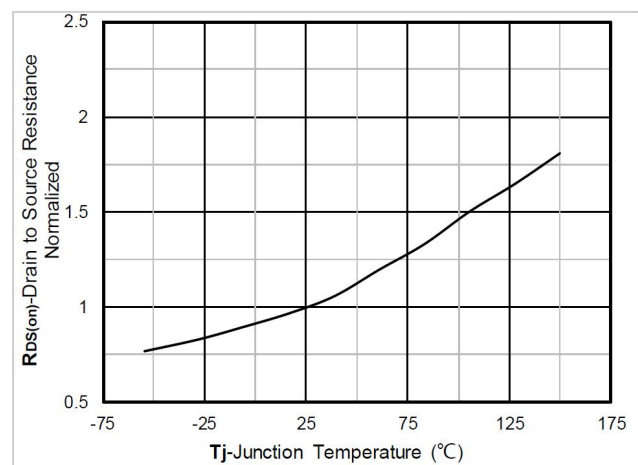
Capacitance Characteristics



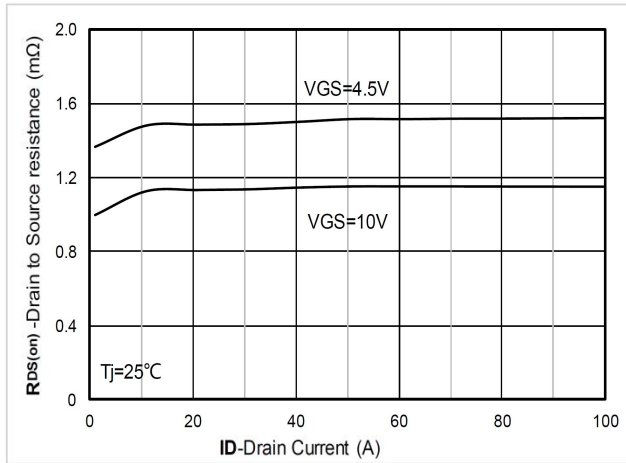
Gate Charge



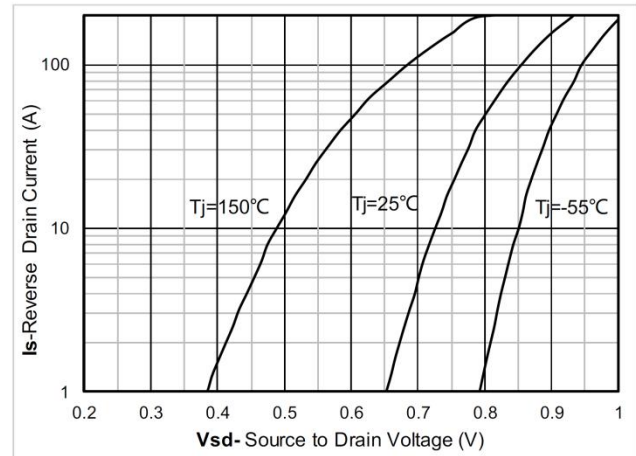
On-Resistance vs Gate to Source Voltage



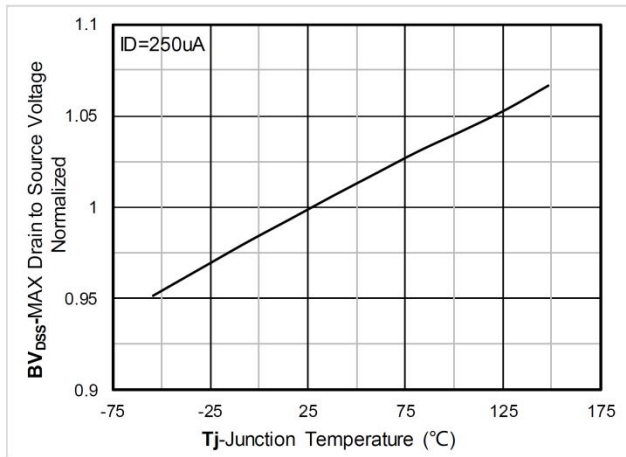
Normalized On-Resistance



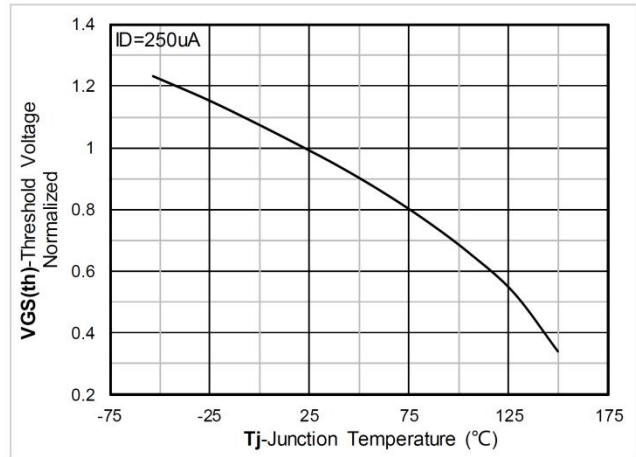
$R_{DS(on)}$ VS Drain Current



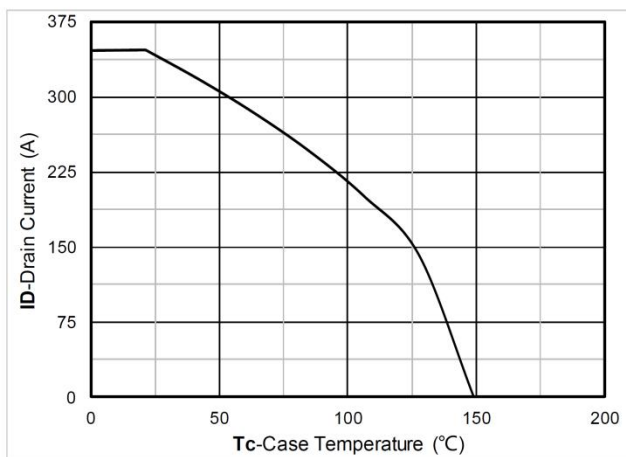
Forward characteristics of reverse diode



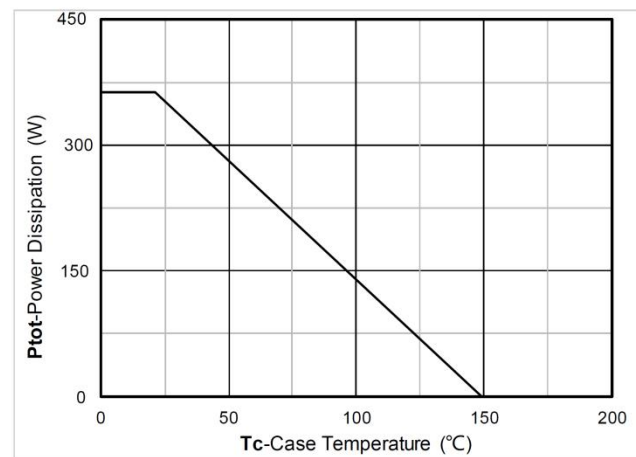
Normalized breakdown voltage



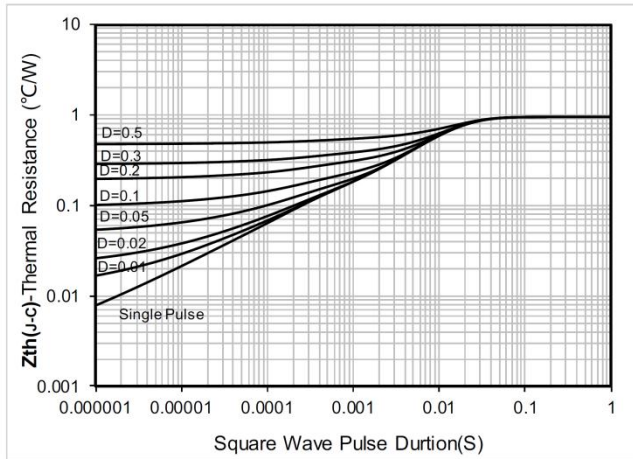
Normalized Threshold voltage



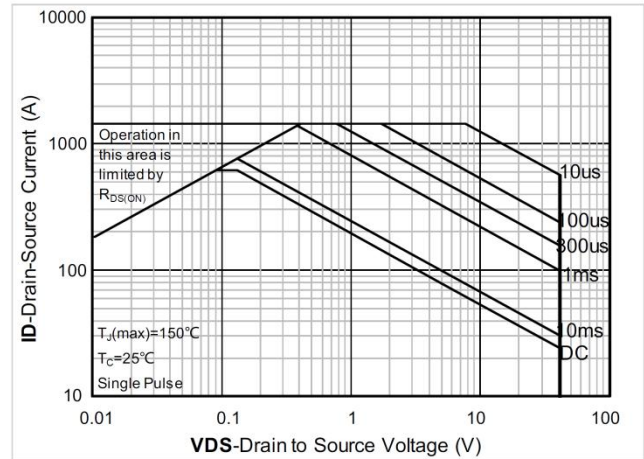
Current dissipation



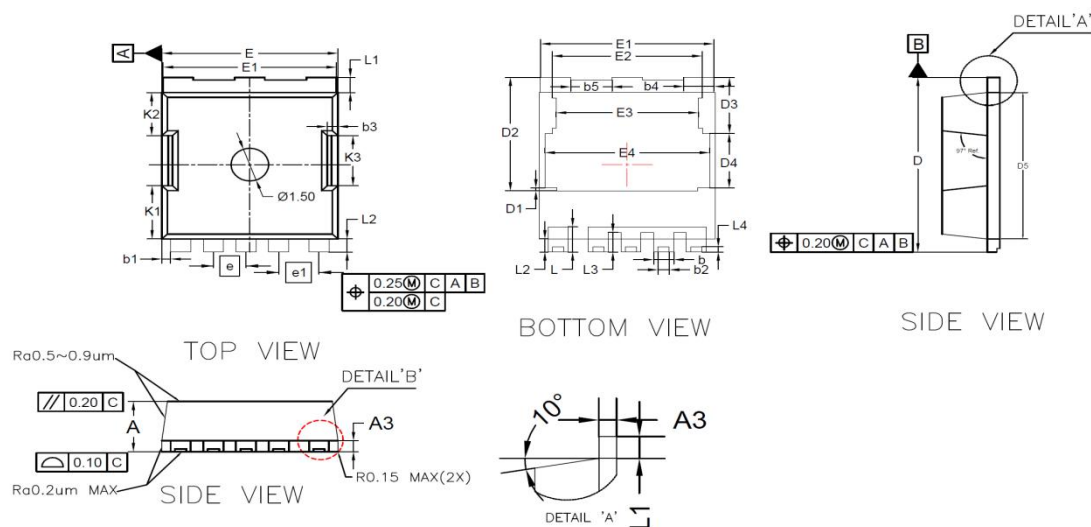
Power dissipation



Maximum Transient Thermal Impedance



Safe Operation Area

sTOLL Package Information


Symbol	Dimensions In Millimeters		
	MIN	NOM	MAX
A	2.262	2.300	2.338
A3	0.492	0.500	0.508
D	7.950	8.000	8.050
D5	6.650	6.700	6.750
E	6.950	7.000	7.050
e	1.30 BCS		
e1	1.60 BCS		
D1	0.130 ref		
D2	5.150	5.200	5.250
D3	2.520	2.570	2.620
D4	2.450	2.500	2.550
b	0.750	0.800	0.850
b1	0.350 ref		
b2	0.350	0.450	0.550
b3	0.400	0.425	0.450
b4	1.100	1.200	1.300
b5	1.550	1.650	1.750
L	1.100	1.150	1.200
L1	0.650	0.700	0.750
L2	0.550	0.600	0.650
L3	0.850	0.900	0.950
L4	0.185	0.235	0.285
E1	6.850	6.900	6.950
E2	5.910	5.960	6.010
E3	5.610	5.660	5.710
E4	6.510	6.560	6.610
K1	2.430 ref		
K2	1.970 ref		
K3	2.275	2.300	2.325